

**isc Silicon PNP Power Transistor**

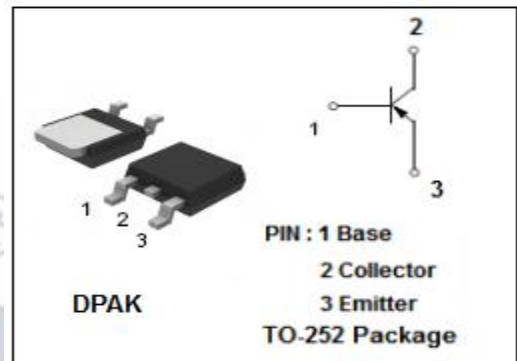
**MJD350**

**DESCRIPTION**

- Collector–Emitter Sustaining Voltage–  
:  $V_{CEO(SUS)} = -300\text{ V(Min)}$
- DC Current Gain–  
:  $h_{FE} = -30(\text{Min}) @ I_C = -50\text{ mA}$
- Low Collector Saturation Voltage–  
:  $V_{CE(sat)} = -1.0\text{ V(Max.)} @ I_C = -50\text{ mA}$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

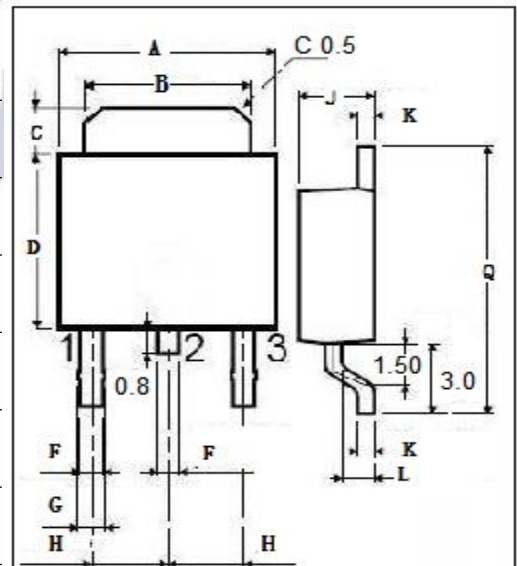
**APPLICATIONS**

- Designed for high voltage and general purpose applications



**ABSOLUTE MAXIMUM RATINGS(Ta=25°C)**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-300	V
$V_{CEO}$	Collector-Emitter Voltage	-300	V
$V_{EBO}$	Emitter-Base Voltage	-3	V
$I_C$	Collector Current-Continuous	-0.5	A
$P_C$	Collector Power Dissipation $T_C=25^\circ\text{C}$	20	W
$T_j$	Junction Temperature	150	°C
$T_{stg}$	Storage Temperature Range	-65~150	°C



DIM	mm	
	MIN	MAX
A	6.40	6.60
B	5.20	5.40
C	1.15	1.35
D	5.70	6.10
F	0.65	
G	0.75	
H	2.10	2.50
J	2.10	2.40
K	0.40	0.60
L	0.90	1.10
Q	9.90	10.1

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	6.25	°C/W

**isc Silicon PNP Power Transistor****MJD350****ELECTRICAL CHARACTERISTICS****T<sub>c</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = -1.0mA; I <sub>B</sub> = 0	-300		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = -1.0mA; I <sub>E</sub> = 0	-300		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -1.0mA; I <sub>C</sub> = 0	-3		V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -50mA; I <sub>B</sub> = -5mA		-1.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -300V; I <sub>E</sub> = 0		-0.1	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -3V; I <sub>C</sub> = 0		-0.1	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = -50mA; V <sub>CE</sub> = -10V	30	240	